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List of Patents and Publications  
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Information Disclosure Statement

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APPLICANT: Waldrip et al.

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REFERENCE DESIGNATION

| Ex'r<br>Init | Document No. | Date | U.S. Patent Documents<br>Name    | Sub<br>Class | Class | File Date               |
|--------------|--------------|------|----------------------------------|--------------|-------|-------------------------|
|              | Document No. | Date | Foreign Patent Documents<br>Name | Sub<br>Class | Class | Translation<br>Yes X No |

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Examiner:

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